Adam Babinski

List of Publications by Year
in descending order

121 papers	1,553 citations	361413 20 h-index	345221 36 g-index
121 all docs	121 docs citations	121 times ranked	1806 citing authors

#	Article	IF	Citations
1	Pressure-Driven Phase Transitions in Bulk HfS₂. Acta Physica Polonica A, 2022, 141, 95-98.	0.5	9
2	The effect of dielectric environment on the brightening of neutral and charged dark excitons in WSe2 monolayer. Applied Physics Letters, 2022, 120, .	3.3	5
3	Quantification of Exciton Fine Structure Splitting in a Two-Dimensional Perovskite Compound. Journal of Physical Chemistry Letters, 2022, 13, 4463-4469.	4.6	20
4	Layered SnSe nanoflakes with anharmonic phonon properties and memristive characteristics. Applied Surface Science, 2022, 599, 153983.	6.1	9
5	Raman spectroscopy of GaSe and InSe post-transition metal chalcogenides layers. Faraday Discussions, 2021, 227, 163-170.	3.2	43
6	Excitonic Complexes in n-Doped WS₂ Monolayer. Nano Letters, 2021, 21, 2519-2525.	9.1	35
7	The optical response of artificially twisted MoS$$_2$$ bilayers. Scientific Reports, 2021, 11, 17037.	3.3	10
8	Resonance and antiresonance in Raman scattering in GaSe and InSe crystals. Scientific Reports, 2021, 11, 924.	3.3	6
9	Exposing the trion's fine structure by controlling the carrier concentration in hBN-encapsulated MoS₂. Nanoscale, 2021, 13, 18726-18733.	5.6	14
10	Anisotropic Optical and Vibrational Properties of GeS. Nanomaterials, 2021, 11, 3109.	4.1	7
11	The optical signature of few-layer ReSe2. Journal of Applied Physics, 2020, 128, .	2.5	17
12	Valley polarization of singlet and triplet trions in a WS₂ monolayer in magnetic fields. Physical Chemistry Chemical Physics, 2020, 22, 19155-19161.	2.8	16
13	Neutral and charged dark excitons in monolayer WS₂. Nanoscale, 2020, 12, 18153-18159.	5.6	22
14	Breathing modes in few-layer MoTe2 activated by h-BN encapsulation. Applied Physics Letters, 2020, 116, .	3.3	8
15	The effect of metallic substrates on the optical properties of monolayer MoSe2. Scientific Reports, 2020, 10, 4981.	3.3	10
16	Energy Spectrum of Two-Dimensional Excitons in a Nonuniform Dielectric Medium. Physical Review Letters, 2019, 123, 136801.	7.8	56
17	Valley polarization of excitonâ€“polaritons in monolayer WSe₂ in a tunable microcavity. Nanoscale, 2019, 11, 9574-9579.	5.6	17
18	Tuning carrier concentration in a superacid treated MoS2 monolayer. Scientific Reports, 2019, 9, 1989.	3.3	18

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19	Emission Excitation Spectroscopy in WS₂ Monolayer Encapsulated in Hexagonal BN. Acta Physica Polonica A, 2019, 136, 624-627.	0.5	4
20	Disorder-induced natural quantum dots in InAs/GaAs nanostructures. Opto-electronics Review, 2018, 26, 73-79.	2.4	1
21	Raman scattering from the bulk inactive outâ€“ofâ€“plane $${{f{B}}}_{{f{2}}{f{g}}}^{{f{1}}}$$ mode in fewâ€“layer MoTe2. Scientific Reports, 2018, 8, 17745.	3.3	12
22	Anomalous Raman Scattering In Few Monolayer MoTe2. MRS Advances, 2017, 2, 1539-1544.	0.9	1
23	Resonant quenching of Raman scattering due to out-of-plane A1g/Aâ€²1 modes in few-layer MoTe2. Nanophotonics, 2017, 6, 1281-1288.	6.0	16
24	Raman scattering excitation spectroscopy of monolayer WS2. Scientific Reports, 2017, 7, 5036.	3.3	63
25	Relative Reflection Difference as a Method for Measuring the Thickness of the Exfoliated MoSe2 Layers. Acta Physica Polonica A, 2017, 132, 316-318.	0.5	0
26	Quadexciton cascade and fine-structure splitting of the triexciton in a single quantum dot. Europhysics Letters, 2016, 113, 17004.	2.0	4
27	Raman scattering of few-layers MoTe ₂. 2D Materials, 2016, 3, 025010.	4.4	67
28	Energy spectrum of confined positively charged excitons in single quantum dots. Physical Review B, 2016, 94, .	3.2	2
29	The excited spin-triplet state of a charged exciton in quantum dots. Journal of Physics Condensed Matter, 2016, 28, 365301.	1.8	3
30	Raman Spectroscopy of Shear Modes in a Few-Layer MoS₂. Acta Physica Polonica A, 2016, 129, A-132-A-134.	0.5	3
31	The Effect of Substrate on Vibrational Properties of Single-Layer MoS_2. Acta Physica Polonica A, 2016, 130, 1172-1175.	0.5	3
32	Raman spectroscopy of few-layer MoSe2 in wide range of temperature. , 2016, , .		0
33	The disorder-induced Raman scattering in Au/MoS2 heterostructures. AIP Advances, 2015, 5, .	1.3	27
34	Excitonic complexes in natural InAs/GaAs quantum dots. Physical Review B, 2015, 91, .	3.2	30
35	Resonant Raman Scattering in MoS2. Materials Research Society Symposia Proceedings, 2015, 1726, 7.	0.1	0
36	Resonant Raman scattering in MoS 2 â€"From bulk to monolayer. Solid State Communications, 2014, 197, 53-56.	1.9	108

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37	Confocal Microscope Studies of MoS₂Layer Thickness. Acta Physica Polonica A, 2014, 126, 1207-1208.	0.5	1
38	Magnetic Field Effect on the Excitation Spectrum of a Neutral Exciton in a Single Quantum Dot. Acta Physica Polonica A, 2014, 126, 1066-1068.	0.5	1
39	Multiphonon resonant Raman scattering in MoS₂. Applied Physics Letters, 2014, 104, 092106.	3.3	118
40	Optical spectroscopy on semiconductor quantum dots in high magnetic fields. Comptes Rendus Physique, 2013, 14, 121-130.	0.9	6
41	Optical Properties of Molybdenum Disulfide (MoS_2). Acta Physica Polonica A, 2013, 124, 849-851.	0.5	42
42	Properties of Excitons in Quantum Dots with a Weak Confinement. Acta Physica Polonica A, 2013, 124, 781-784.	0.5	2
43	Intershell Exchange Interaction in Charged GaAlAs Quantum Dots. Acta Physica Polonica A, 2013, 124, 785-787.	0.5	4
44	Renormalization of effective mass in self-assembled quantum dots due to electron-electron interactions. Journal of Physics: Conference Series, 2013, 456, 012002.	0.4	0
45	The effect of In-flush on the optical anisotropy of InAs/GaAs quantum dots. Journal of Applied Physics, 2012, 111, 033510.	2.5	6
46	Fine Structure of Neutral Excitons in Single GaAlAs Quantum Dots. Acta Physica Polonica A, 2012, 122, 988-990.	0.5	6
47	The Fine Structure of a Triexciton in Single InAs/GaAs Quantum Dots. Acta Physica Polonica A, 2012, 122, 991-993.	0.5	4
48	Single-photon emission from the natural quantum dots in the InAs/GaAs wetting layer. Physical Review B, 2011, 84, .	3.2	7
49	Quantum Confinement in InAs/GaAs Systems with Self-Assembled Quantum Dots Grown Using In-Flush Technique. Acta Physica Polonica A, 2011, 119, 624-626.	0.5	0
50	Quantum confinement in MOVPE-grown structures with self-assembled InAs/GaAs quantum dots. Journal of Physics: Conference Series, 2010, 245, 012079.	0.4	0
51	Energy shell structure of a single InAs/GaAs quantum dot with a spin-orbit interaction. Physical Review B, 2009, 79, .	3.2	11
52	Threeâ€dimensional localization of excitons in the InAs/GaAs wetting layer â€“ magnetospectroscopic study. Physica Status Solidi (B): Basic Research, 2009, 246, 850-853.	1.5	3
53	Effects of magnetic fields on free excitons in CuInSe2. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1086-1088.	0.8	6
54	Charged and neutral excitons in natural quantum dots in the InAs/GaAs wetting layer. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2078-2080.	2.7	5

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55	Natural quantum dots in the InAsâˆ•GaAs wetting layer. Applied Physics Letters, 2008, 92, 171104.	3.3	27
56	Single-exciton energy shell structure in InAs/GaAs quantum dots. Physical Review B, 2008, 78, .	3.2	10
57	Neutral and Charged Excitons Localized in the InAs/GaAs Wetting Layer. Acta Physica Polonica A, 2008, 114, 1055-1060.	0.5	3
58	Optical readout of charge and spin in a self-assembled quantum dot in a strong magnetic field. Europhysics Letters, 2007, 79, 47005.	2.0	1
59	Zerogfactors and nonzero orbital momenta in self-assembled quantum dots. Physical Review B, 2007, 75, .	3.2	39
60	Excitonic Fock-Darwin Spectrum Of A Single Quantum Dot. AIP Conference Proceedings, 2007, , .	0.4	0
61	Quantum oscillations of the luminescence from a modulation-doped GaAsâˆ•InGaAsâˆ•GaAlAs quantum well. Applied Physics Letters, 2006, 88, 051909.	3.3	3
62	Ground-state emission from a singleInAsâˆ•GaAsself-assembled quantum dot structure in ultrahigh magnetic fields. Physical Review B, 2006, 74, .	3.2	29
63	Fock-Darwin spectrum of a single InAs/GaAs quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3748-3751.	0.8	17
64	Optical spectroscopy of a single InAs/GaAs quantum dot in high magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 288-291.	2.7	3
65	Emission from a highly excited singleInAsâˆ•GaAsquantum dot in magnetic fields: An excitonic Fock-Darwin diagram. Physical Review B, 2006, 74, .	3.2	40
66	Dynamics of Excitation Transfer Inside InAs/GaAs Quantum Dot System. Acta Physica Polonica A, 2006, 110, 219-224.	0.5	2
67	Optical Spectroscopy of Quantum Dots in High Magnetic Fields. Acta Physica Polonica A, 2006, 110, 275-286.	0.5	3
68	Influence of Intersubband Scattering on the Magnetic Field Dependence of the Conductivity Tensor. Acta Physica Polonica A, 2006, 110, 337-344.	0.5	1
69	Single-dot spectroscopy in high magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 190-193.	2.7	15
70	Electron and Hole States in Vertically Coupled Self-Assembled InGaAs Quantum Dots. AIP Conference Proceedings, 2005, , .	0.4	1
71	Fine structure in the excitonic emission ofInAsâˆ•GaAsquantum dot molecules. Physical Review B, 2005, 71, .	3.2	47
72	MAGNETO-LUMINESCENCE OF A SINGLE LATERAL ISLAND FORMED IN A TYPE - II GaAs/AlAs QW. , 2005, , .		0

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73	Electronic and Structural Properties of Interdiffused Self-Assembled Quantum Dots from Magneto-Photoluminescence. Japanese Journal of Applied Physics, 2004, 43, 2088-2092.	1.5	5
74	Excitonic Energy Shell Structure of Self-Assembled InGaAs/GaAs Quantum Dots. Physical Review Letters, 2004, 92, 187402.	7.8	111
75	MAGNETO-LUMINESCENCE OF A SINGLE LATERAL ISLAND FORMED IN A TYPE - II GaAs/AlAs QW. International Journal of Modern Physics B, 2004, 18, 3807-3812.	2.0	2
76	Enhanced excitonâ€“LO phonon coupling in doped quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 400-404.	2.7	0
77	Electronic structure of InAs/GaAs self-assembled quantum dots studied by high-excitation luminescence in magnetic fields up to. Physica B: Condensed Matter, 2004, 346-347, 432-436.	2.7	9
78	Electronâ€“hole complexes in self-assembled quantum dots in strong magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 211-214.	2.7	0
79	Photoluminescence excitation spectroscopy of InAs/GaAs quantum dots in high magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 603-606.	2.7	2
80	Localization of Excitons in the Wetting Layer Accompanying Self-Assembled InAs/GaAs Quantum Dots. Acta Physica Polonica A, 2004, 105, 547-552.	0.5	3
81	Emission from Mesoscopic-Size Islands Formed in a GaAs/AlAs Double Layer Structure. Acta Physica Polonica A, 2004, 106, 367-381.	0.5	9
82	Optical determination of the dopant concentration in the Î´-doping layer. Journal of Applied Physics, 2002, 92, 163-167.	2.5	5
83	Free-to-bound and interband recombination in the photoluminescence of a dense two-dimensional electron gas. Physical Review B, 2002, 65, .	3.2	4
84	Determination of Si ?-Doping Concentration in GaN by Electroreflectance. Physica Status Solidi (B): Basic Research, 2002, 234, 868-871.	1.5	3
85	Post-growth thermal treatment of self-assembled InAs/GaAs quantum dots. Thin Solid Films, 2002, 412, 84-88.	1.8	22
86	Rapid thermal annealing of InAs/GaAs quantum dots under a GaAs proximity cap. Applied Physics Letters, 2001, 79, 2576-2578.	3.3	105
87	Quantum corrections to the electrical conduction in an AlGaN/GaN heterostructure. Applied Physics A: Materials Science and Processing, 2001, 72, 691-698.	2.3	3
88	Step-like Photoluminescence Dynamics in Field-Effect Structures Containing Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 227, 605-612.	1.5	1
89	Electroluminescence from a forward-biased Schottky barrier diode on modulation Si Î´-doped GaAs/InGaAs/AlGaAs heterostructure. Applied Physics Letters, 2001, 78, 3992-3994.	3.3	7
90	Dynamics of Photoexcited Carriers in GaInAs/GaAs Quantum Dots. Acta Physica Polonica A, 2001, 100, 379-386.	0.5	3

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91	InGaAs/GaAs Quantum Dot Interdiffusion Induced by Cap Layer Overgrowth. Materials Research Society Symposia Proceedings, 2000, 618, 179.	0.1	1
92	The Effect of Electron Occupation on the Photoluminescence from the Self-Organised InGaAs/GaAs Quantum Dots. Physica Status Solidi A, 2000, 178, 313-316.	1.7	1
93	Transport and quantum electron mobility in the modulation Si Î´-doped pseudomorphic GaAs/In[sub 0.2]Ga[sub 0.8]As/Al[sub 0.2]Ga[sub 0.8]As quantum well grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2000, 77, 999.	3.3	18
94	Photoluminescence from InGaAs/GaAs Quantum Dots in a High Electric Field. , 2000, , 395-404.		0
95	Electroreflectance bias-wavelength mapping of the modulation Si Î´-doped pseudomorphic GaAs/InGaAs/AlGaAs structure. Applied Physics Letters, 1999, 75, 2088-2090.	3.3	11
96	Si and C Î´-doping for device applications. Journal of Crystal Growth, 1998, 195, 54-57.	1.5	2
97	Electrically modulated photoluminescence in self-organized InGaAs/GaAs quantum dots. Applied Physics Letters, 1998, 73, 2811-2813.	3.3	8
98	Electron transfer efficiency of Si Î´-modulation-doped pseudomorphic GaAs/In0.2Ga0.8As/AlxGa1â^'xAs quantum wells. Applied Physics Letters, 1998, 72, 2322-2324.	3.3	16
99	Optical Properties of Self-Organized InGaAs/GaAs Quantum Dots in Field-Effect Structures. Materials Research Society Symposia Proceedings, 1998, 536, 269.	0.1	0
100	The persistent photoconductivity effect in modulation Si Î´-doped pseudomorphic In0.2Ga0.8As/GaAs quantum well structure. Applied Physics Letters, 1997, 71, 1664-1666.	3.3	15
101	Subband electron densities of Si Î´-doped pseudomorphic In0.2Ga0.8As/GaAs heterostructures. Applied Physics Letters, 1997, 70, 3582-3584.	3.3	8
102	GaSb Dots Grown on GaAs Surface by Metalorganic Chemical Vapour Deposition. Acta Physica Polonica A, 1995, 88, 974-976.	0.5	7
103	Orientation of Metastable EL2 under Uniaxial Stress. Acta Physica Polonica A, 1995, 87, 137-140.	0.5	0
104	Splitting of the metastableEL2 acceptor state. Physical Review B, 1994, 50, 10656-10660.	3.2	4
105	Symmetry of the Acceptor-Like State of the EL2 Defect in the Metastable Configuration. Materials Science Forum, 1993, 143-147, 1051-1056.	0.3	1
106	Ordering of the EL2 Defects in the Metastable State. Materials Science Forum, 1993, 143-147, 1007-1012.	0.3	1
107	Deep Level Transient Spectroscopy Measurements of an Acceptor-like State of Metastable EL2 in GaAs and GaAsP. Acta Physica Polonica A, 1993, 84, 673-676.	0.5	0
108	Electrical Properties of an Acceptor-like State of Metastable EL2 in n-type GaAs under Uniaxial Stress. Acta Physica Polonica A, 1992, 82, 908-910.	0.5	0

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109	Hydrostatic Pressure Spectroscopy of the Vanadium Luminescence in GaAs. Acta Physica Polonica A, 1992, 82, 837-840.	0.5	0
110	Hydrostatic-Pressure Deep Level Transient Spectroscopy Study of the Heteroantisite Antimony Level in GaAs. Acta Physica Polonica A, 1992, 82, 841-844.	0.5	0
111	Pressure-induced negative charge state of theEL2 defect in its metastable configuration. Physical Review B, 1991, 43, 2070-2080.	3.2	31
112	The Pressure Dependence of Transition Metal-Related Levels in GaAs. Acta Physica Polonica A, 1991, 79, 323-327.	0.5	2
113	FFirst TSC and DLTS Measurements of Low Temperature GaAs. Acta Physica Polonica A, 1991, 80, 413-416.	0.5	4
114	Acceptor-Like Level of the EL2 Defect in its Metastable Configuration. Acta Physica Polonica A, 1991, 79, 129-132.	0.5	0
115	Passivation of a Bulk Defect E_c-0.22 eV in GaAs by Contact with Phosphoric Acid. Acta Physica Polonica A, 1991, 79, 277-280.	0.5	0
116	Properties of the Fe Acceptor Level in Inp Under Hydrostatic Pressure. , 0, , .		0
117	Capacitance measurements on self-organised MOCVD-grown InGaAs quantum dots. , 0, , .		0
118	Ultrafast time-resolved photoluminescence measurements on InGaAs/GaAs quantum dots. , 0, , .		0
119	Low-temperature light emission in a forward-biased Schottky diode with a n-doped channel. , 0, , .		0
120	The effect of electric field on the self-organized quantum dots. , 0, , .		0
121	Post-growth thermal treatment of the InAs/GaAs quantum dots. , 0, , .		0